Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C

Supporting Information

Flexible organic/inorganic heterojunction transistors with low operating voltage

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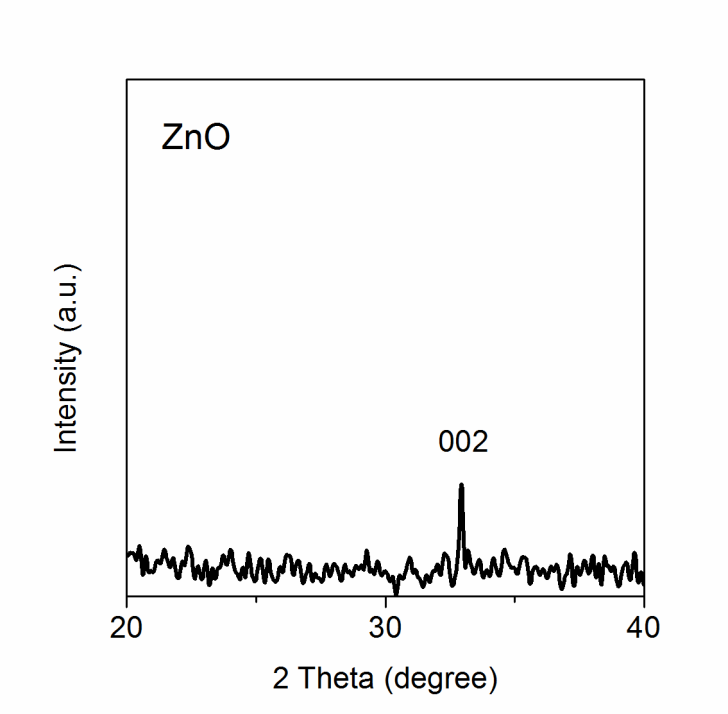

Fig. S1. XRD pattern of ZnO film.

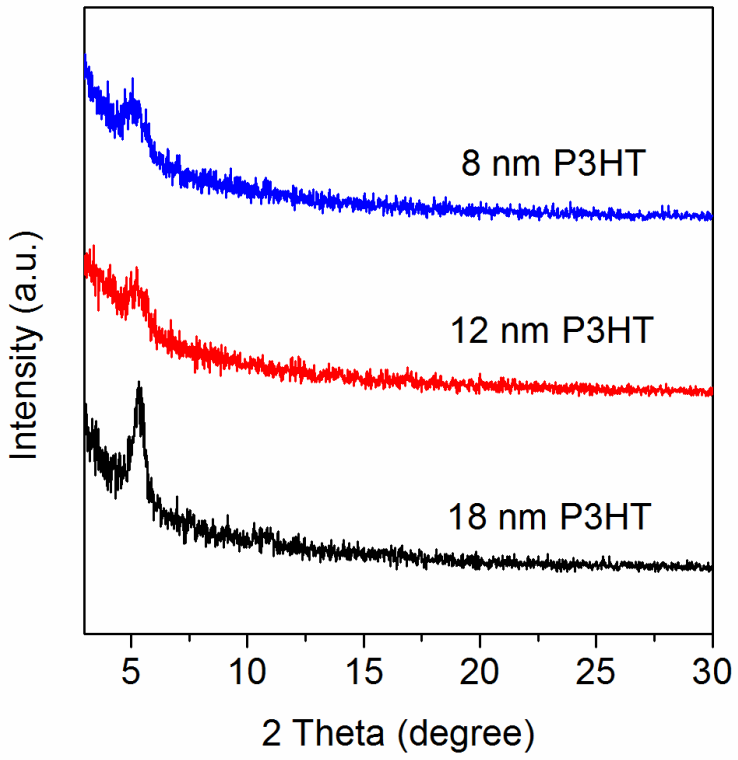

Fig. S2. XRD patterns of different thicknesses of P3HT on ZnO.

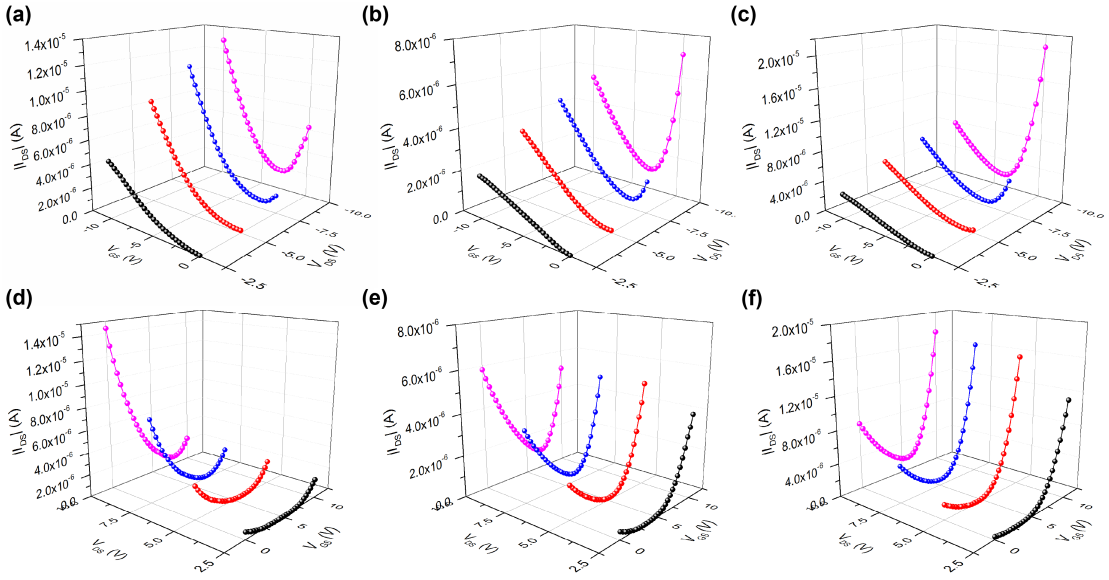

Fig. S3. Transfer characteristics of the ambipolar transistors with (a) 18 nm (b) 12 nm and (c) 8 nm P3HT in hole enhancement mode at various V_{DS}. Transfer characteristics of the ambipolar transistors with (d) 18 nm (e) 12 nm and (f) 8 nm P3HT in electron enhancement mode at various V_{DS}.

Table S1. Characteristics of the ambipolar transistors with various thinknesses of P3HT: roughness of P3HT, threshold voltage in hole-enhancement mode and threshold voltage in electron-enhancement mode.

	8 nm P3HT	**12 nm P3HT**	**18 nm P3HT**
Roughness (R_{rms})	0.59 nm	0.76 nm	1.17 nm
Threshold voltage (hole-enhancement mode)	-3.8	-3.1	-2.8 V
Threshold voltage (electron-enhancement mode)	5.8 V	6.9 V	7.9 V